

CLAIMS

- [1] A III nitride single-crystal manufacturing method wherein a liquid layer of 200 μm or less thickness is formed in between a substrate and a III nitride source-material baseplate, and III nitride single crystal is grown onto the face of said substrate on its liquid-layer side.
- [2] A III nitride single-crystal manufacturing method set forth in claim 1, wherein said substrate in at least a superficial layer along the liquid layer is formed of a III nitride single crystal, and said III nitride source-material baseplate is formed of a III nitride polycrystal.
- [3] A III nitride single-crystal manufacturing method set forth in claim 1, wherein said substrate in at least a superficial layer along the liquid layer, and said III nitride source-material baseplate are formed of a III nitride single crystal, and the face of said substrate on its liquid-layer side is a Group-III-atom surface; and the face of said III nitride source-material baseplate on its liquid-layer side is a nitrogen-atom surface.
- [4] A III nitride single-crystal manufacturing method set forth in any of claims 1 through 3, wherein said liquid layer includes an element of at least one kind selected from the group consisting of elements constituting said III nitride single crystal.
- [5] A III nitride single crystal obtained according to the III nitride single-crystal manufacturing method set forth in any of claims 1 through 4.
- [6] A semiconductor device incorporating the III nitride single crystal set

forth in claim 5.